

Product Introduction

Our Ge (Germanium) wafers are available in diameters from 2" to 6", with thickness options ranging from 175µm to 625µm to suit various process requirements. Offered in undoped, N-type (Sb), and P-type (Ga) variants with resistivity from 0.005 to over 30 Ω·cm, these wafers feature <100> and <111> orientations, low TTV/bow/warp ($\leq 25\mu\text{m}$), and epi-ready surface finishes. With low etch pit density ($< 3000/\text{cm}^2$), our Ge wafers provide a reliable substrate for high-efficiency optoelectronic and photovoltaic applications.

Applications

- Substrates for III-V multi-junction solar cells
- Infrared optics and lenses
- Photodetectors and infrared sensors
- Epitaxial growth platform for GaAs and other III-V compound semiconductor devices

GERMANIUM (GE) WAFER SPECIFICATIONS			
DIAMETER	2 INCH ~ 6 INCH		
Thickness	175um / 200um / 400um / 500um / 625um		
Type/Dopant	Undoped	N/Sb	P/Ga
Resistivity ($\Omega \cdot \text{cm}$)	> 30	> 0.005	$> 0.005-0.04$
EP(/cm ²)	< 3000	< 3000	0
Orientation	<100>, <111>		
TTV	$\leq 25\mu\text{m}$		
Bow	$\leq 25\mu\text{m}$		
Wrap	$\leq 25\mu\text{m}$		
Surface	E/E, P/E, P/D		
Epi-ready	Yes		